WILLAS

RoHS COMPLIANT

SOT-323 Plastic-Encapsulate Diodes

MMBD2004SW

SWITCHING DIODE

FEATURES

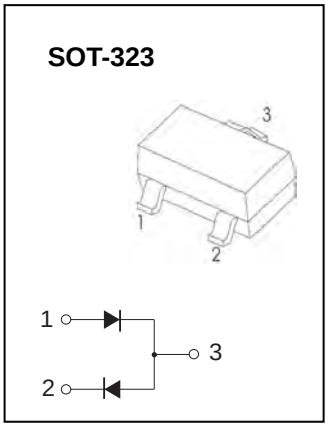
CMSD2004S type is a silicon switching dual in series diode manufactured by the epitaxial planar process, designed for applications requiring high voltage capability. Power dissipation

Pb-Free package is available

RoHS product for packing code suffix ”G”

Halogen free product for packing code suffix “H”

Moisture Sensitivity Level 1



MARKING : B6D

Maximum Ratings @T_A=25℃

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak reverse voltage	V_{RM}	300	V
DC Blocking Voltage	V_R	240	V
Peak Repetitive Current	I_O	225	mA
Continuous Forward Current	I_F	225	mA
Peak Repetitive Forward Current	I_{FRM}	625	mA
Forward Surge Current tp=1 μs	I_{FSM}	4.0	A
Forward Surge Current tp=1 s	I_{FSM}	1.0	A
Power Dissipation	Pd	250	mW
Junction temperature	T_J	150	℃
Storage temperature range	T_{STG}	-55~+150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	I_R= 100μA	240		V
Reverse voltage leakage current	I_R	V_R=240V		0.1	mA
Forward voltage	V_F	I_F=100mA		1	V
Diode capacitance	C_D	V_R=0V,f=1MHz		5	pF
Reveres recovery time	t_{rr}	I_F=I_R=30mA,R_L=100Ω		50	ns

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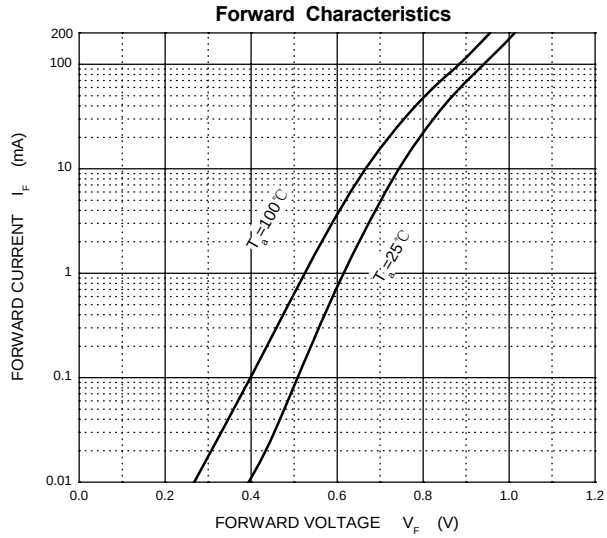
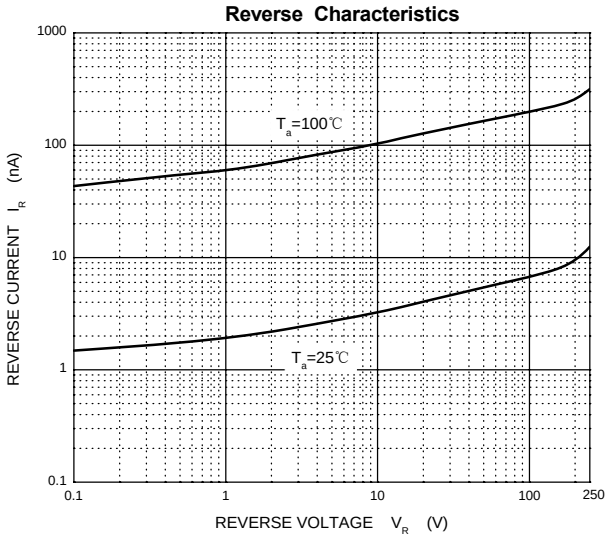
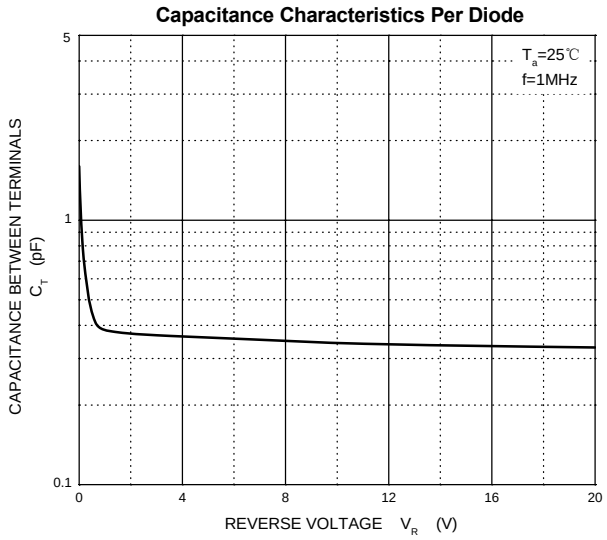
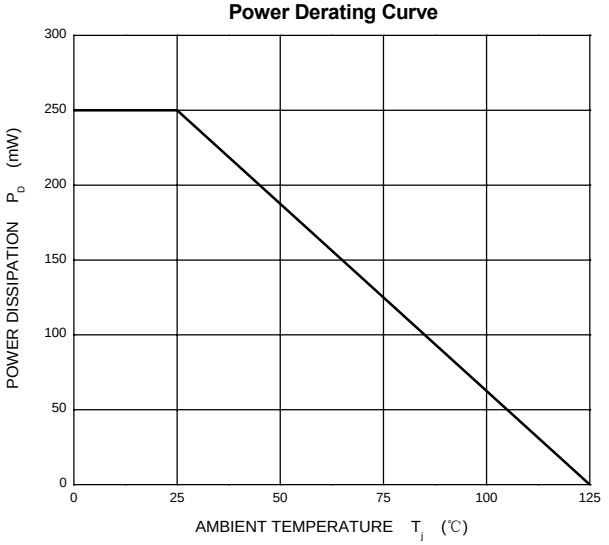
Typical Characteristics



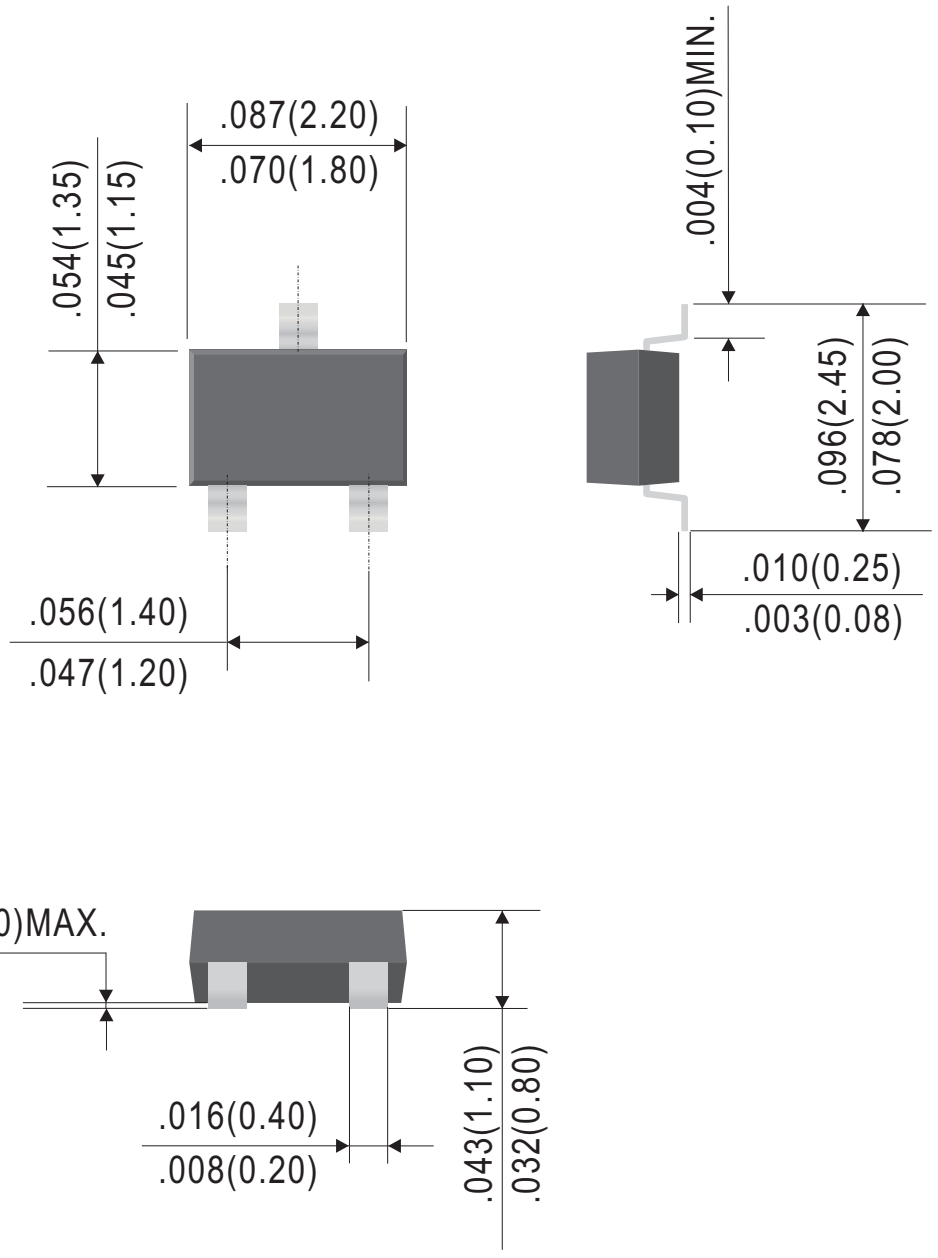






Outline Drawing

SOT-323



Dimensions in inches and (millimeters)

Rev.D